

FLX 3300-R

AUTOMATED STRESS Measurement

Toho FLX-3300-R Thin Film Stress Measurement Systems offer industry standard capabilities for mass production and research facilities that demand accurate stress measurements on various films and substrates up to 300mm in diameter. Incorporating KLA-Tencor's patented "Dual Wave-length" technology, Toho FLX Series tools determine and analyze surface stress caused by deposited thin films. The Toho FLX systems offer out-standing value in a variety of comprehensive Stress Measurement Solutions.



Standard Features

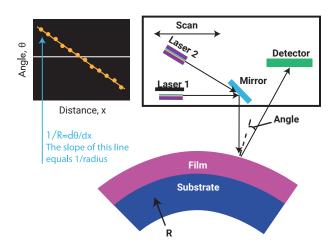
Comprehensive Data Analysis

Intuitive Windows 7 based analysis software displays any combination of stress, time, surface deflection, or reflected light intensity measurements.

- Calculation of biaxial modulus of elasticity, linear expansion coefficient, stress uniformity, and file subtraction
- Trend plotting for Statistical Process Control (SPC)
- Calculation of water diffusion coefficient in dielectric films
- Automatic recalculation of stress when film or substrate thickness is corrected
- 2-D and 3-D views of wafer topography
- Plotting of the measured stress-temperature curve

Advanced Laser Technology

The FLX series feature KLA-Tencor's patented dual wavelength technology, which enables the system to select the wavelength most suitable for challenging films such as silicon nitride.In addition only one moving element in the optical component ensures low vibration and high accuracy.



FLX stress
measurement
systems use the
laser lever
technique to
measure changes in
pre and post
deposition surface
radii and then
correlates these
measurements into
a stress value.

Applications

In general, stress is induced when materials of dissimilar coefficients of thermal expansion are bonded together. Films may behave similarly at high temperatures but as films are cooled, materials may contract / expand differently, thus causing stress in the film. With a stressed film, defects such as dislocations, voids, and cracking may occur. The FLX stress measurement system helps troubleshoot applications listed below:

- · Aluminum stress-induced voids
- Passivation cracking (nitride/oxide)
- · Stress-induced dislocations in Si
- Tungsten Silicide cracking
- Stress increase in oxides during temperature cycling
- Matching metallization expasion on GaAs
- Si cracking due to high film stress

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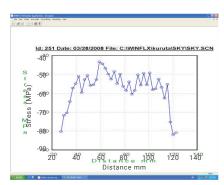
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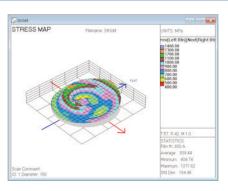
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Providing fast and accurate measurements and enhanced ease of use at room temperature, the automated rotating stage model offers increased flexibility. The universal stage is recipe programmable for developing 3D measurements and serves as an optimal monitoring device for verifying film uniformity across the entire 300mm substrate surface.

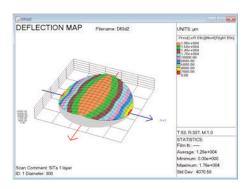




StressTemperature Graph



3-D Stress Map



3-D Deflection Map

Specifications

Performance

Scan Range Programmable up to 300mm

Measurement Range 1 to 4,000MPa¹

Repeatability 1.3MPa²

Accuracy Less than 2.5% or 1 MPa (whichever is larger)

Minimim Radius 2.0m Maximum Radius 33km

Wafer Sizes (mm) 100, 150, 200, 300mm

Minimum Scan Step 0.02mm

Compliance Class IIIa 670nm / 780nm 4mW lasers compliant

with 21CFR, Chapter 1 Subchapter J

Notes:

1725µm wafer thickness for 10,000Å thin film

 $^{2}(1s): 1 \times 10^{7} \text{ dyne/cm}^{2}$

U.S. Patent No.'s 5134303 and 5248889

KLA Tencor

The Toho FLX Series incorporates the original KLA-Tencor design and patents.

Options

- · 3D Analysis Software
- Calibration Mirror Standards
- Calibration Wafer Standards
- Substrate Adaptor Rings
- Offline Software

Computer Specifications

Win 10 OS, Intel Core i5 2.66 GHz, 2GB RAM, 500 GB HD, USB port, DVD-RW optical drive

Specifications subject to change.

